

## MD2103DFP

# High voltage NPN power transistor for standard definition CRT display

## Features

- State-of-the-art technology:
  - Diffused collector "enhanced generation"
- Stable performance versus operating temperature variation
- Low base drive requirement
- Tight h<sub>FE</sub> range at operating collector current
- Fully insulated power package UL compliant
- Integrated free wheeling diode

## Applications

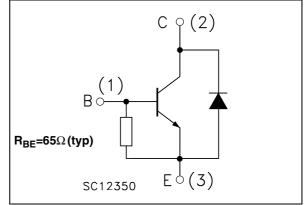
Horizontal deflection output for TV

## Description

The MD2103DFP is manufactured using diffused collector in planar technology adopting new and enhanced high voltage structure. The new MD product series show improved silicon efficiency briging updated performance to the horizontal deflection stage.

# TO-220FP

#### Figure 1. Internal schematic diagram



#### Table 1. Device summary

Order code	Marking	Package	Packing
MD2103DFP	MD2103DFP	TO-220FP	Tube

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## 1 Electrical ratings

Table 2.	Absolute maximum rating
	Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> =0)	1500	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> =0)	700	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> =0)	7	V
Ι <sub>C</sub>	Collector current	6	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	9	Α
Ι <sub>Β</sub>	Base current	3	Α
P <sub>tot</sub>	Total dissipation at $T_c  arrow 5^{\circ}C$	38	W
V <sub>INS</sub>	Insulation withstand voltage (RMS) from all three leads to external heatsink	1500	v
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
Τ <sub>J</sub>	Max. operating junction temperature	150	°C

#### Table 3.Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	3.3	°C/W

## 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$ 

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> =0)	$V_{CE} = 1500V$ $V_{CE} = 1500V$ $T_{C} = 125^{\circ}C$			0.2 2	mA mA
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> =0)	V <sub>EB</sub> = 5V	50		125	mA
V <sub>(BR)EBO</sub>	Emitter-base brakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 700mA		11		V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	I <sub>C</sub> = 3A I <sub>B</sub> =0.75A			1.8	v
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 3A I <sub>B</sub> =0.75A			1.5	V
h <sub>FE</sub> <sup>(1)</sup>	DC current gain		6.5	17 6	9.5	
t <sub>s</sub> t <sub>f</sub>	Inductive load Storage time Fall time	$\begin{split} I_{C} = 3A & f_{h} = 16 \text{kHz} \\ I_{B(on)} = 0.5A & V_{BE(off)} = -2.7V \\ L_{BB(off)} = 6.3 \mu \text{H} \\ (\text{see Figure 12}) \end{split}$		3.8 0.25		μs μs
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 3A			2	V

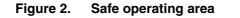
#### Table 4. Electrical characteristics

Note:

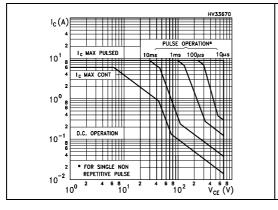
Note (1) Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5%

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## 2.1 Electrical characteristics (curves)



#### Figure 3. Derating curve



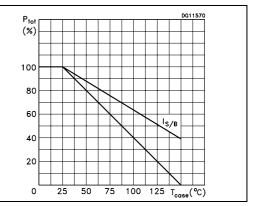


Figure 4. Output characteristics

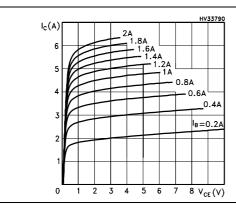
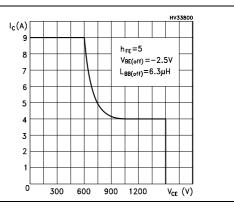


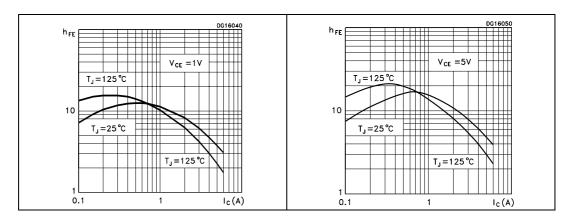
Figure 5. Reverse biased SOA

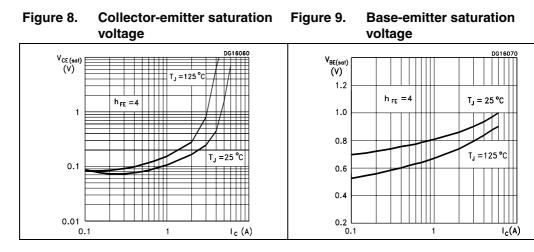


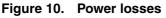
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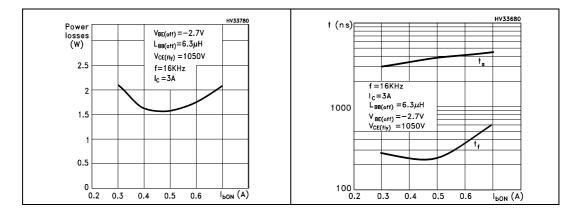
Figure 7. DC current gain





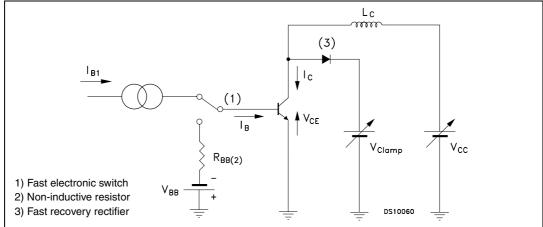






#### 2.2 Test circuits



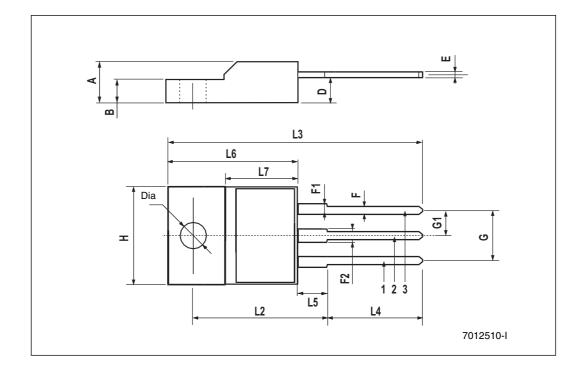


## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



	TO-220FP mechanical data						
Dim.		mm.			inch		
Dilli.	Min.	Тур	Max.	Min.	Тур.	Max.	
А	4.40		4.60	0.173		0.181	
В	2.5		2.7	0.098		0.106	
D	2.5		2.75	0.098		0.108	
Е	0.45		0.70	0.017		0.027	
F	0.75		1.00	0.030		0.039	
F1	1.15		1.50	0.045		0.067	
F2	1.15		1.50	0.045		0.067	
G	4.95		5.20	0.195		0.204	
G1	2.40		2.70	0.094		0.106	
Н	10		10.40	0.393		0.409	
L2		16			0.630		
L3	28.6		30.6	1.126		1.204	
L4	9.80		10.60	0.385		0.417	
L5	2.9		3.6	0.114		0.141	
L6	15.90		16.40	0.626		0.645	
L7	9		9.30	0.354		0.366	
Dia	3		3.2	0.118		0.126	



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## 4 Revision history

#### Table 5.Document revision history

Date	Revision	Changes
27-May-2008 1		First release



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